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- (71) **Applicant: APPLIED MATERIALS, INC.** [US/US];
3050 Bowers Avenue, Santa Clara, California 95054 (US).
- (72) **Inventors: CITLA, Bhargav S.;** c/o Applied Materials, Inc., 3050 Bowers Avenue, Santa Clara, California 95054 (US). **ASRANI, Soham;** c/o Applied Materials, Inc., 3050 Bowers Avenue, Santa Clara, California 95054 (US). **RUBNITZ, Joshua;** c/o Applied Materials, Inc., 3050 Bowers Avenue, Santa Clara, California 95054 (US). **NEWMANI, Srinivas D.;** c/o Applied Materials, Inc., 3050 Bowers Avenue, Santa Clara, California 95054 (US). **YIEH, Ellie Y.;** c/o Applied Materials, Inc., 3050 Bowers Avenue, Santa Clara, California 95054 (US).

- (74) **Agent: CAMPBELL, Quinten;** Kilpatrick Townsend & Stockton LLP, Mailstop: IP Docketing-22, 1100 Peachtree Street, Suite 2800, Atlanta, Georgia 30309 (US).

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- (54) **Title: DIRECTIONAL SELECTIVE DEPOSITION**

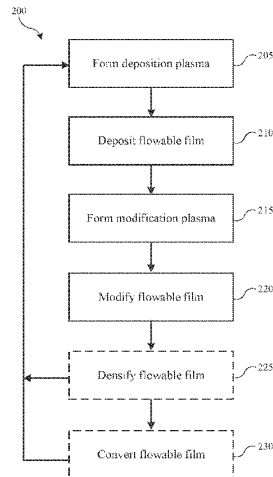


FIG. 2

- (57) **Abstract:** Exemplary processing methods may include forming a plasma of a silicon-containing precursor. The methods may include depositing a flowable film on a semiconductor substrate with plasma, effluents of the silicon-containing precursor. The processing region may be at least partially defined between a faceplate and a substrate support on which the semiconductor substrate is seated. A bias power may be applied to the substrate support from a bias power source. The methods may include forming a plasma of a hydrogen-containing precursor within the processing region of the semiconductor processing chamber. The methods may include etching the flowable film from a sidewall of the feature within the semiconductor substrate with plasma effluents of the hydrogen-containing precursor. The methods may include densifying remaining flowable film within the feature defined within the semiconductor substrate with plasma, effluents of the hydrogen-containing precursor.

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